WEITRON

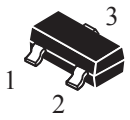
WAN202K / WAP202K
WAN217

Surface Mount Switching Diode

Lead(Pb)-Free

SWITCHING DIODE
100m AMPERRES
80 VOLTS

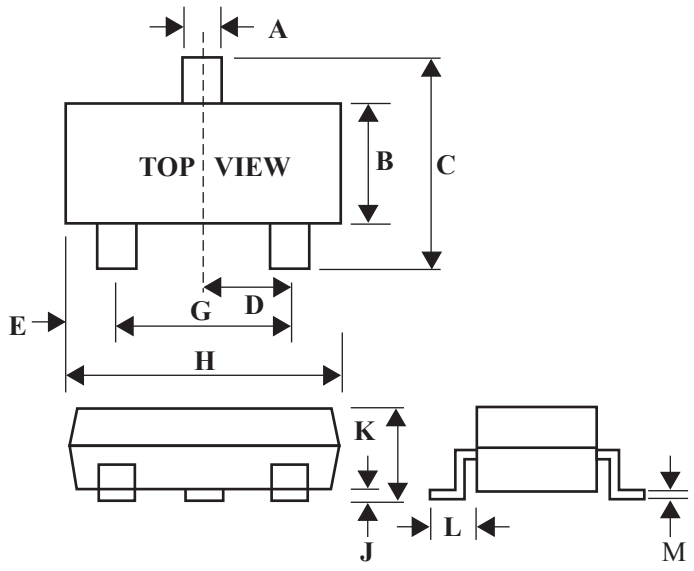
Features:
*Low Current Leakage
*Low Forward Voltage
*Ultra High Speed Switching
*Small Outline Surface Mount SOT-23 Package



SOT-23

SOT-23 Outline Dimensions

Unit:mm



Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25

Maximum Ratings (EACH DIODE)

Characteristic	Symbol	WAN202K	WANP202K	WAN217	Unit
Reverse Voltage	V_R	80			Volts
Forward Current	I_F	100			mAdc
Peak Forward Surge Current	I_{FM}	300			mAdc

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board *1, TA=25°C Derate Above 25°C	P_D	200 1.6	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction and Storage Temperature	T_J, T_{stg}	-55 to + 150	°C

*1 ER-5=1.0x0.75x0.062 in

Electrical Characteristics (TA=25°C Unless Otherwise Note) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage (I_{BR}=100 μAdc)	V_{BR}	80		Vdc
Reverse Voltage Leakage Current V_R=70V	I_R		0.1	μAdc
Diode Capacition (V_R=6Vdc, f=1.0MHz)	C_D		3.5	PF
Forward Voltage (I_F=100 mAdc)	V_F		1.2	Vdc
Reverse Recovery Time (Figure 1.) I_R=5.0 mAdc, V_R=6.0Vdc	t_{rr}		4.0	nS

Device Marking

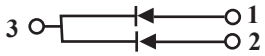
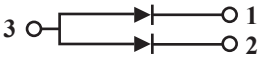
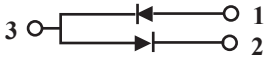
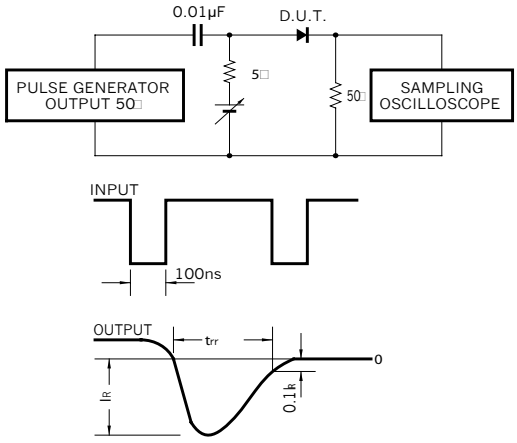
Item	Marking	Eqivalent Circuit diagram
WAN202K	A4	
WAP202K	A1	
WAN217	A7	

Figure 1. Recovery Time Equivalent Test Circuit



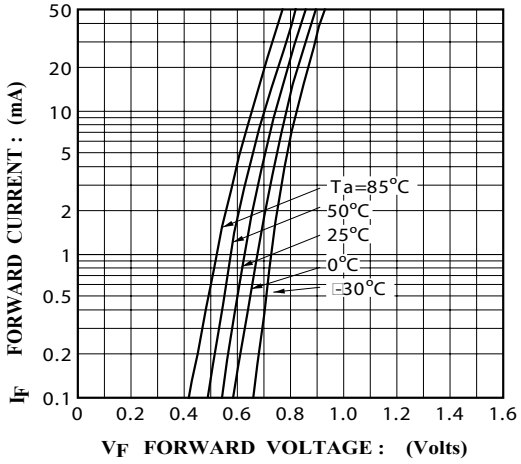


Fig.2 Forward characteristics

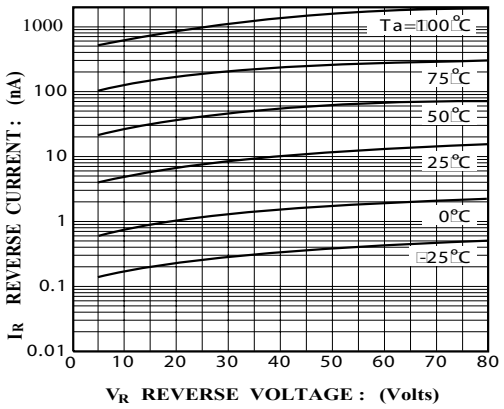


Fig.3 Reverse characteristics

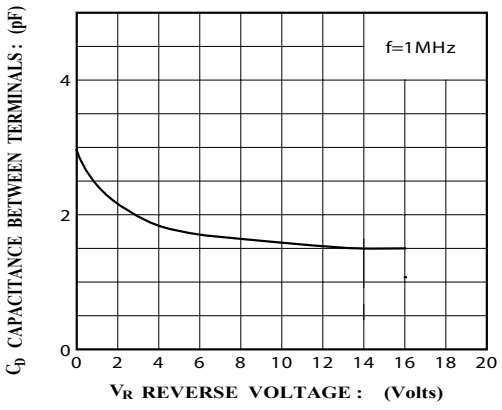


Fig.4 Capacitance